



A351 PCT USA - 067515.0161

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Bong-Cheol Kim

Serial No. : 10/089,479

Filed : March 28, 2002

For : APPARATUS AND METHOD FOR FORMING SINGLE CRYSTALLINE
NITRIDE SUBSTRATE USING HYDRIDE VAPOR PHASE EPITAXY
AND LASER BEAM

Group A Unit: 2812

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REQUEST FOR A CORRECTED OFFICIAL FILING RECEIPT

Assistant Commissioner for Patents
Office of Initial Patent Examination
Customer Service Center
Washington, D.C. 20231

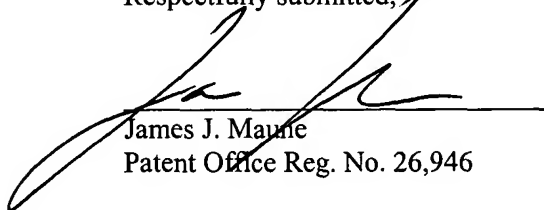
Sir:

We have received the Official Filing Receipt for the application identified above. On the Official Filing Receipt, we noted an error in the title of the invention. Please correct as follows:

--APPARATUS AND METHOD FOR FORMING SINGLE
CRYSTALLINE **NITRIDE** SUBSTRATE USING HYDRIDE VAPOR PHASE EPITAXY
AND LASER BEAM--.

Applicant hereby respectfully requests the issuance of a corrected Official Filing Receipt.

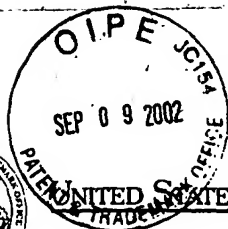
Respectfully submitted,



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APPLICATION NUMBER	FILING DATE	GRP ART UNIT	FIL FEE REC'D	ATTY. DOCKET NO	DRAWINGS	TOT CLAIMS	IND CLAIMS
10/089,479	03/28/2002	2812	520	A35109 PCT USA	4	11	2

CONFIRMATION NO. 1153

21003
BAKER & BOTTS
30 ROCKEFELLER PLAZA
NEW YORK, NY 10112

FILING RECEIPT



OC000000008267496

Date Mailed: 06/26/2002

Receipt is acknowledged of this nonprovisional Patent Application. It will be considered in its order and you will be notified as to the results of the examination. Be sure to provide the U.S. APPLICATION NUMBER, FILING DATE, NAME OF APPLICANT, and TITLE OF INVENTION when inquiring about this application. Fees transmitted by check or draft are subject to collection. Please verify the accuracy of the data presented on this receipt. If an error is noted on this Filing Receipt, please write to the Office of Initial Patent Examination's Filing Receipt Corrections, facsimile number 703-746-9195. Please provide a copy of this Filing Receipt with the changes noted thereon. If you received a "Notice to File Missing Parts" for this application, please submit any corrections to this Filing Receipt with your reply to the Notice. When the USPTO processes the reply to the Notice, the USPTO will generate another Filing Receipt incorporating the requested corrections (if appropriate).

Applicant(s)

Bong-Cheol Kim, Cheongju-shi, JAPAN;

Domestic Priority data as claimed by applicant

THIS APPLICATION IS A 371 OF PCT/KR00/00935 08/21/2000

Foreign Applications

REPUBLIC OF KOREA 1999-41892 09/30/1999

Projected Publication Date: Not Applicable, filed prior to November 29, 2000

Non-Publication Request: No

Early Publication Request: No

** SMALL ENTITY **

Title

Apparatus and method for forming single crystalline nitride substrate using hydride vapor phase epitaxy and laser beam

NITRIDE

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